

AMENDMENTS TO THE SPECIFICATION:

Please replace paragraph [0123] with the following amended paragraph:

[0123] A base film 101 is formed over the substrate 100. The base film may have a single layer structure or a layered structure. The base film is formed in order. to prevent an alkaline metal such as Na or an alkaline earth metal contained in the substrate 100 from spreading in a semiconductor film and exerting an adverse effect on semiconductor element characteristics. The base film can be therefore formed by using an insulating film such as silicon oxide, silicon nitride, silicon oxynitride, titanium oxide, or titanium nitride, which is capable of suppressing the spread of an alkaline metal or an alkaline earth metal into the semiconductor film. The base film can be formed by using a conductive film of titanium or the like. In this case, the conductive film is oxidized by heat treatment or the like in a manufacturing step. Specifically, a material of the base film may be selected from materials having high adhesion with a gate electrode material. For example, a base film of titanium oxide (TiOx) is preferably formed when Ag is used for the gate electrode. Titanium oxide has both base film function and adhesion improving function. As another material of the base film, a 3d transition element (Sc, Ti, V, Cr, Mn, Fe, Co, Ni, Cu, or Zn), or an oxide, a nitride, or an oxynitride thereof may be used.

Please replace paragraph [0140] with the following amended paragraph:

[0140] The diameter of each of nozzles 104 and the amount of droplets can be set according to the volume of the conductor, that is the volume of the depression of the insulating film, and the characteristics to the droplet material, such as viscosity ~~viscosity~~.

Please replace paragraph [0149] with the following amended paragraph:

[0149] The gate insulating ~~insulating~~ film may have a layered structure or a single layer structure. The gate insulating film can use an insulator of an inorganic material such as silicon oxide, silicon nitride, or silicon oxynitride; or an insulator of an organic material such as polysilazane or polyvinyl alcohol.